

L Number	Hits	Search Text	DB	Time stamp
1	11082	SAC or "self-aligned contact"	USPAT; EPO; JPO; IBM_TDB	2003/03/26 13:36
2	44	(SAC or "self-aligned contact") and bias and endpoint	USPAT; EPO; JPO; IBM_TDB	2003/03/26 13:41
3	214	(contact or opening or via) and sidewall and spacer and (gate or electrode) and endpoint	USPAT; EPO; JPO; IBM_TDB	2003/03/26 14:34
4	9	(bias adj voltage) same endpoint	USPAT; EPO; JPO; IBM_TDB	2003/03/26 14:08
5	151	(bias adj voltage) and endpoint	USPAT; EPO; JPO; IBM_TDB	2003/03/26 17:02
6	401	(contact or opening or via) and spacer and (gate or electrode) and endpoint	USPAT; EPO; JPO; IBM_TDB	2003/03/26 15:41
7	76	(contact or opening or via) and spacer and (gate or electrode) and bias and endpoint	USPAT; EPO; JPO; IBM_TDB	2003/03/26 15:42
8	1		USPAT; EPO; JPO; IBM_TDB	2003/03/26 16:24
11	54	("silicon oxide" or SiO or dielectric or insulating) and polysilicon and (tetraethylorthosilicate or TEOS) and gate and spacer and (bias adj voltage)	USPAT; EPO; JPO; IBM_TDB	2003/03/26 17:01
12	90	((bias adj voltage) and endpoint) and etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/03/26 17:02